

VRFC0010-BD

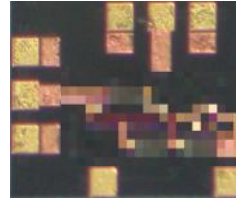


8-15 GHz Single Bit GaAs MMIC Phase Shifters

Preliminary Datasheet v2

Features

- Frequency Range: 8-15GHz
- Single Bit 45°, 90° and 180° Phase Shifters
- 50Ω Matched RF Ports



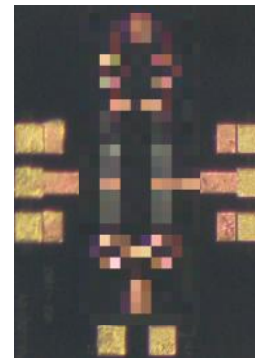
45° Phase Shifter



90° Phase Shifter

Description

The VRFC0010-BD are a set of 8-15 GHz single bit phase shifters. Typical applications include Defence and Instrumentation markets.



180° Phase Shifter

Electrical Specifications

$T=+25^{\circ}\text{C}$ baseplate, $V_{ctrl}=0/-5\text{V}$

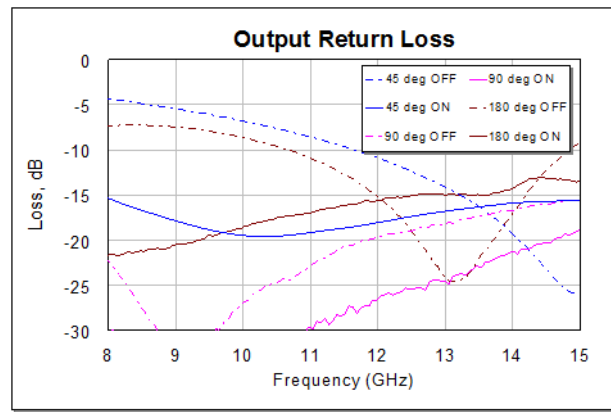
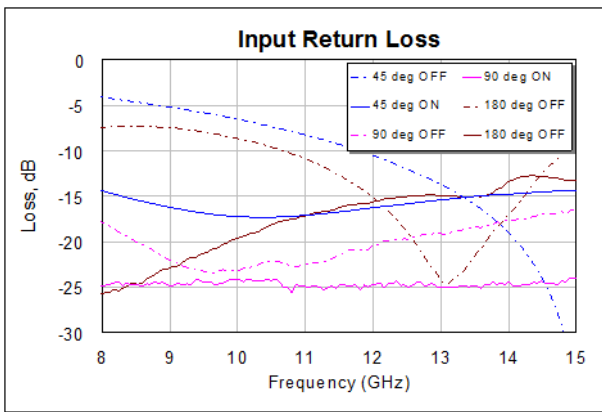
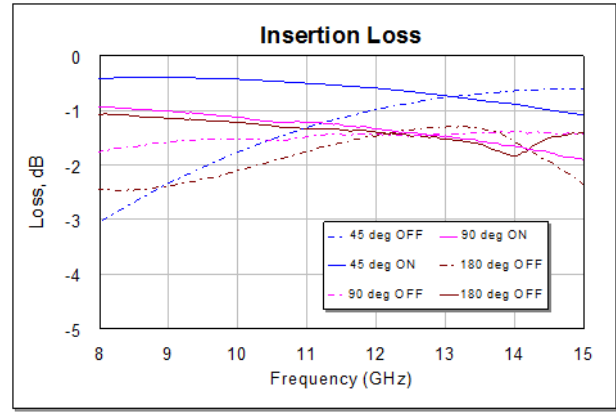
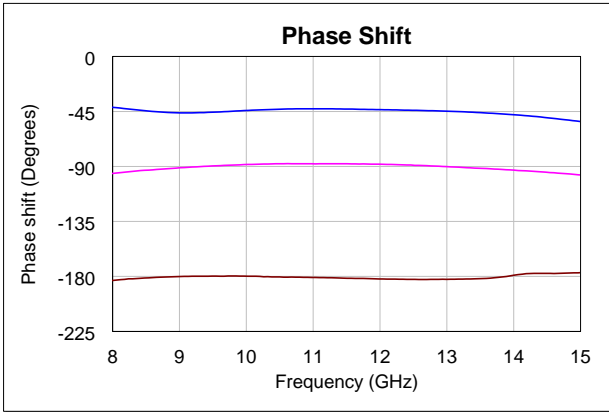
Parameter	Specification			Unit
	Typ. @8GHz	Typ. @11.5GHz	Typ. @15GHz	
45° Phase Shifter	43.8	45.2	50.4	deg
90° Phase Shifter	95.7	87.9	96.9	deg
180° Phase Shifter	183.2	181.4	177	deg
Return Loss of 45° Phase shifter (I/O)	10.12/7.6	13.2/14.2	16.8/17	dB
Return Loss of 90° Phase shifter (I/O)	17.6/21.8	21.5/20.7	16.5/15.7	dB
Return Loss of 180° Phase shifter (I/O)	7.4/7.4	12.7/12.7	9.4/9.4	dB
Insertion Loss of 45° Phase shifter	3	1.1	0.6	dB
Insertion Loss of 90° Phase shifter	1.7	1.4	1.8	dB
Insertion Loss of 180° Phase shifter	2.4	1.6	2.3	dB

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Measured Performance (On-wafer)

$T=+25^{\circ}\text{C}$ baseplate, $V_{ctrl}=0/-5\text{V}$



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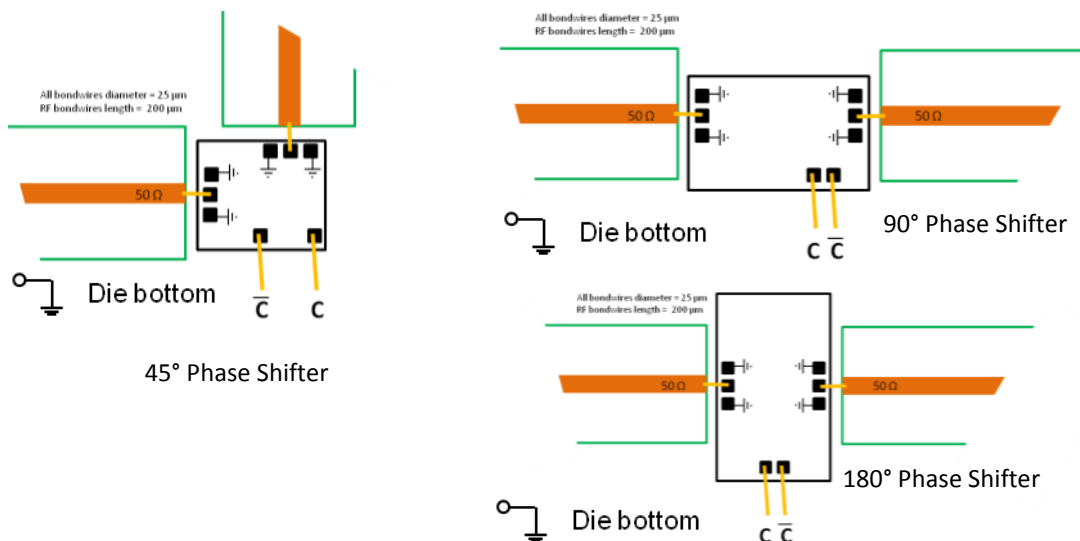
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Recommended Absolute Maximum Ratings ^[1]

Parameter	Symbol	Value	Notes
Control Voltage (+)	V_{ctrl+}	+0.5 V	
Control Voltage (-)	V_{ctrl-}	-7 V	
Control Current	I_{ctrl}	100 μ A	
RF Input Power	RF_{in}	27 dBm	
Junction Temperature	T_j	175°C	For maximum median device lifetime, T_j should be minimised
Storage Temperature	$T_{storage}$	-55 to 150°C	

^[1] Operation outside these conditions may cause permanent damage to the device. Combination of maximum rating conditions may reduce the values. Device performance at these ratings is not implied.

Assembly & Bonding Diagram



	45°	90°	180°
Engineering Die Size	2mm x 1mm	2mm x 1.5mm	2mm x 1.5mm
Est. Production Die Size	0.9mm x 0.6mm	1.3mm x 0.75mm	0.9mm x 1.3mm
Die Thickness	100 μ m	100 μ m	100 μ m
Minimum Bondpad Opening	70 μ m x 70 μ m	70 μ m x 70 μ m	70 μ m x 70 μ m

Minimal length (0.15nH) are recommended for RF bondwires. The RF input and output ports are DC blocked.

GaAs devices are ESD sensitive and precautions should be observed during storage, handling, assembly and testing.

